

SPECIFICATION

參考資料

Device Name : High Voltage Silicon Diode
Type Name : ESJA52-12

1. SCOPE

This specification provide the ratings and the requirements for high voltage silicon diode ESJA52-12 made by FUJI ELECTRIC CO.,LTD.

2. OUT VIEW

Shape and dimensions are described in Fig.

3. IDENTIFICATION

The diode shall be marked with Cathode Mark and Lot No..

4. RATINGS AND CHARACTERISTICS

4.1 ABSOLUTE MAX. RATINGS (Ta=25 °C unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage.		V _{RRM}	12	kVpeak
Non-Repetitive peak forward current.	50Hz Sine-half wave peak value	I _{FSM}	0.5	Apeak
Average forward current.	50Hz Sine Wave	I _{AV}	5	mA
Allowable junction temperature.		T _j	120	°C
Storage temperature range.		T _{stg}	-40~120	°C
Allowable operating case temperature.		T _c	100	°C

4.2 ELECTRICAL CHARACTERISTICS (Ta=25 °C unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Maximum forward voltage drop	IF=10mA	VF	45	V
Maximum reverse current	VR=12kV	I _{R1}	2	μA
Maximum reverse current	VR=12kV, 100°C	I _{R2}	5	μA
Maximum reverse recovery time	IF=2mA, I _R =4mA	t _{rr}	0.08	μS
Maximum junction capacitance	f=1MHz, VR=0V	C _j	2	pF

Fuji Electric Co.,Ltd.
Matsumoto Factory

DATE	NAME	APPROVED	DWG NO.	Fuji Electric Co.,Ltd.	
DRAWN					
CHECKED					

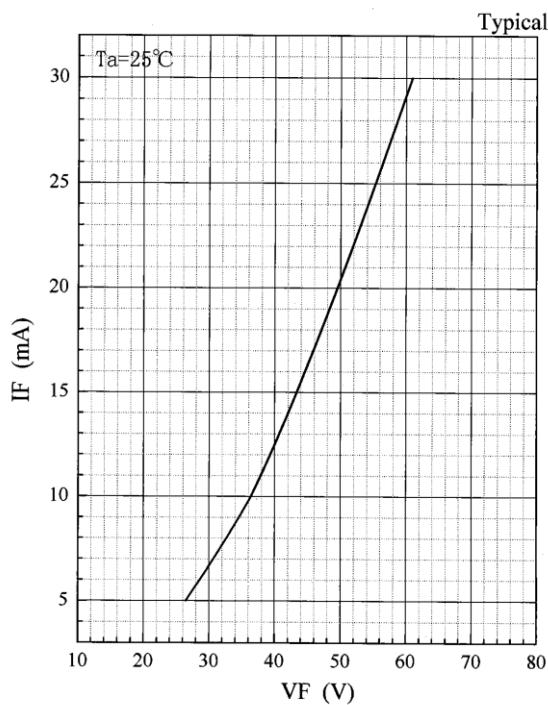


Fig.1 Forward characteristic [VF-IF]

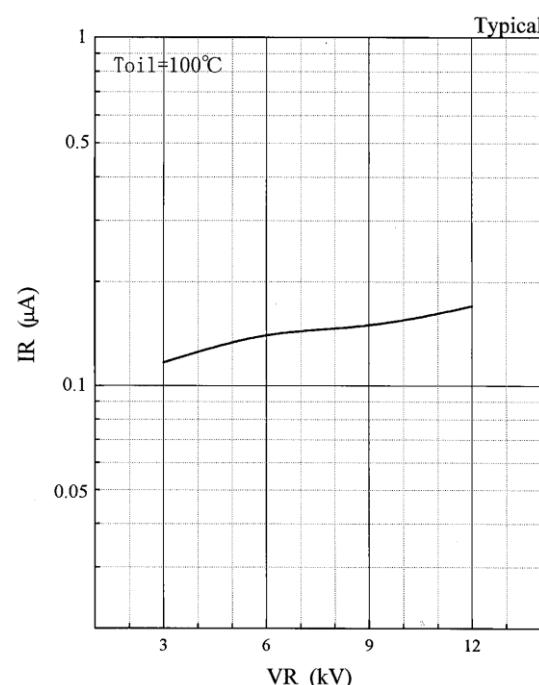


Fig.2 Reverse characteristic [VR-IR]

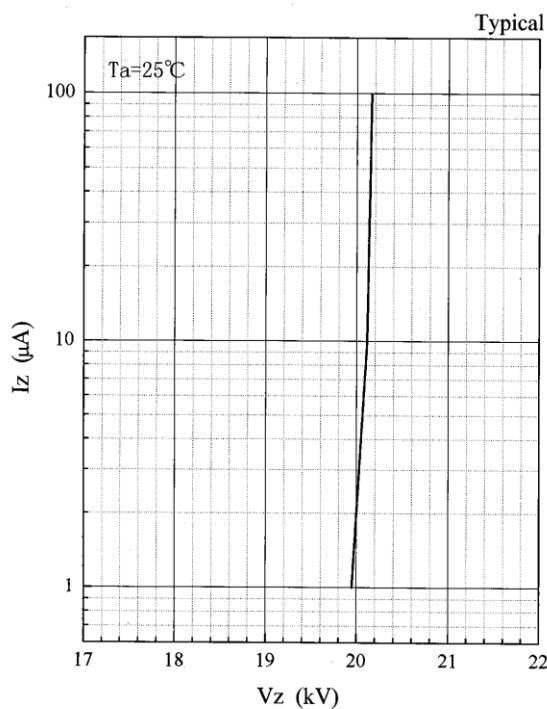


Fig.3 Avalanche characteristic [Vz-Iz]

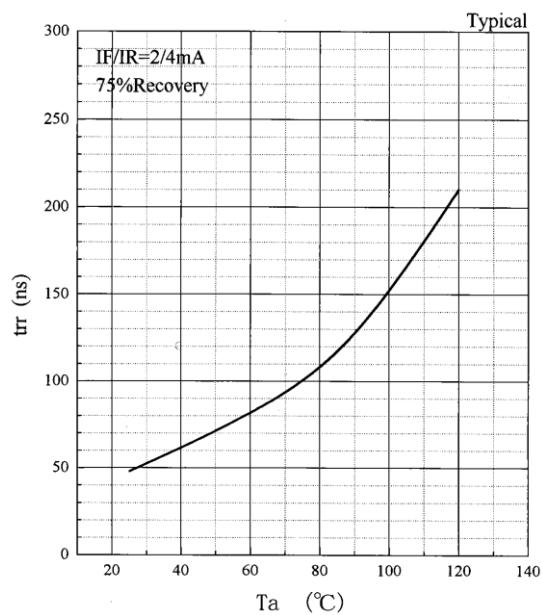


Fig.4 Reverse recovery time characteristic [Ta-trr]

Dimensions

Unit : mm

